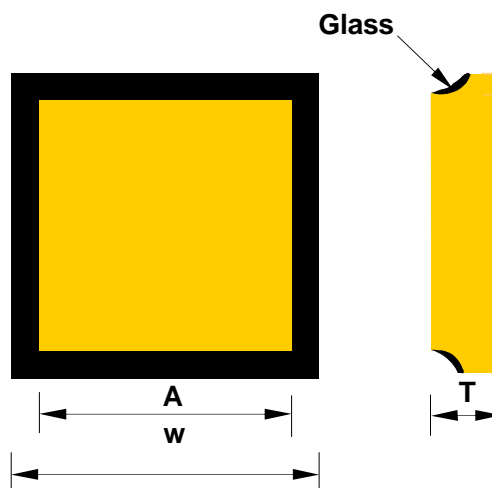




## Super Fast Rectifier GPP Chips

### Features

- i Fully glass passivated -needs no encapsulation
- i Low forward voltage drop( $V_F$ )
- i Metallized surface



### Description

The GPP chips series are diffused silicon, glass passivated rectifier die.

These devices can be supplied to meet customer's requirements.

The prime application for unencapsulated die is in hybrid circuits.

For this reason, a variety of metallized surfaces are available.

Gold is standard for wire bonding, and for soldering application, gold flash chips are supplied.

Electrical Characteristics ( $T_a = 25^\circ\text{C}$  unless specified)

PARAMETER	SYM BOL	SGS84			UNIT
Dimension	W	84±3			mils
Dimension	A	71±3			mils
Dimension	T	200~240			μ m
Forward current	$I_F$	3.0			Amps
Peak Inverse Voltage	$V_B$	200	400	600	Volts
Forward Voltage Drop	$V_F$	≤0.95	≤1.25	≤1.7	Volts
Reverse Recovery Time	$T_{RR}$	≤35	≤35	≤35	ns
Forward Surge current	$I_{FSM}$	120			Amps
Junction Temperature	$T_{JFM}$	175			°C
Reverse Current at 25°C	$I_R$	2			μ A
Storage Temperature	$T_{ST}$	-65 --- 175			°C
Die attach Temperature	$T_d$	375			°C

Note :

Other dimension of GPP chip ranging from 42 mils to 600 mils which is not specified on the list, can also be supplied by special procurement agreement.